

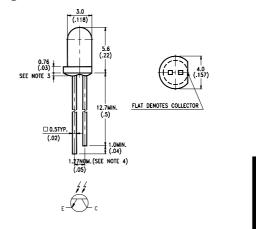
NPN T-1 Modified 3 ϕ **Phototransistor** LTR-209

Package Dimensions

- Features
- Wide range of collector currents.
- · Lens for high sensitivity.
- · Low cost plastic package.

Description

The LTR-209 consist of a NPN silicon phototransistor mounted in a lensed, clear plastic, end looking package. The lensing effect of the package allows an acceptance half angle of 8 ° measured from the optical axis to the half power point. This series is mechanically and spectrally matched to the LTE-209 series of infrared emitting diodes.



Notes:

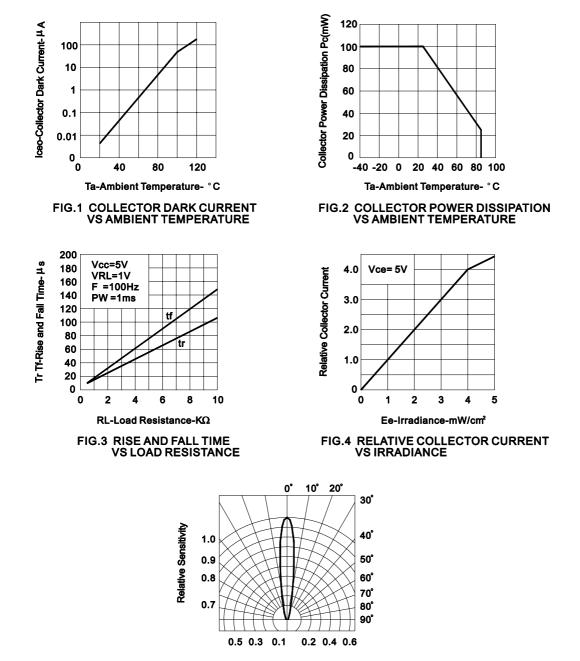
- 1. All dimensions are in millimeters (inches).
- 2. Tolerance is \pm 0.25mm (.010") unless otherwise noted.
- 3. Protruded resin under flange is 1.5mm (.059") max.
- 4. Lead spacing is measured where the leads emerge from the package.
- 5. Specifications are subject to change without notice.

Absolute Maximum Ratings at Ta=25°C

Parameter	Maximum Rating	Unit		
Power Dissipation	100	mW		
Collector-Emitter Voltage	30	V		
Emitter-Collector Voltage	5	V		
Operating Temperature Range	-40°C to +85°C			
Storage Temperature Range	-55°C to +100°C			
Lead Soldering Temperature [1.6mm (.063 in.) from body]	260°C for 5 Seconds			

Electrical Optical Characteristics at Ta=25°C

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Condition
Collector-Emitter Breakdown Voltage	V(BR)CEO	30			V	Ic=1mA Ee=0mW/cm ²
Emitter-Collector Breakdown Voltage	V(BR)ECO	5			V	IE=100 μ A Ee=0mW/cm ²
Collector Emitter Saturation Voltage	VCE(SAT)			0.4	V	Ic=100 μ A Ee=1mW/cm ²
Rise Time	Tr		10		μS	Vcc=5V Ic=1mA
Fall Time	Tf		15		μS	RL=1KΩ
Collector Dark Current	ICEO			100	nA	Vce=10V Ee=0mW/cm ²
On State Collector Current	IC(ON)	1	4		mA	$V_{CE}=5V$ Ee=1mW/cm ² λ =940nm



Typical Electrical/Optical Characteristic Curves (25°C Ambient Temperature Unless Otherwise Noted)

FIG.5 SENSITIVITY DIAGRAM



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Lite-On: LTR-209